



General Description

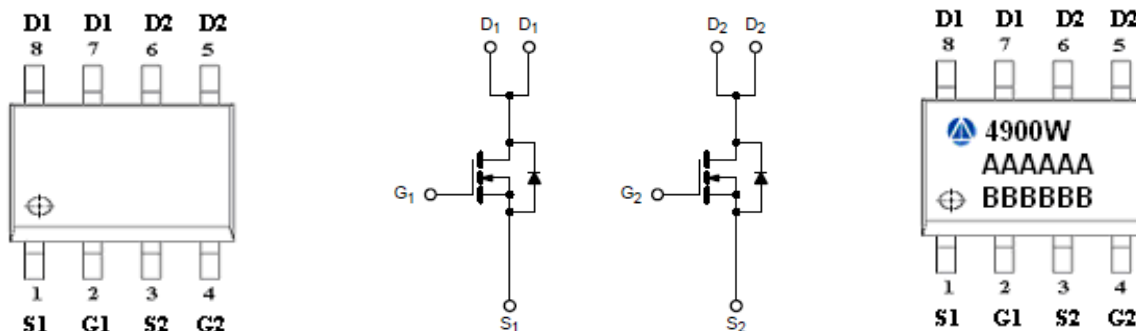
AFN4900W, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- $I_D=6.8A, R_{DS(ON)}=100m\Omega @V_{GS}=10V$
- $I_D=5.6A, R_{DS(ON)}=130m\Omega @V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOP-8P package design

Pin Description (SOP-8P)



Application

- Motor and Load Control
- AD/DC Inverter Systems.
- Power Management in White LED System

Pin Define

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN4900WS8RG	4900W	SOP-8P	Tape & Reel	2500 EA

※ A Lot code

※ B Date code

※ AFN4900WS8RG : 13" Tape & Reel ; Pb- Free ; Halogen -Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	T _A =25°C	6.8
		T _A =70°C	5.6
Pulsed Drain Current	I _{DM}	12	A
Continuous Source Current(Diode Conduction)	I _S	1.5	A
Power Dissipation	P _D	T _A =25°C	2.8
		T _A =70°C	1.8
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	62.5	°C/W

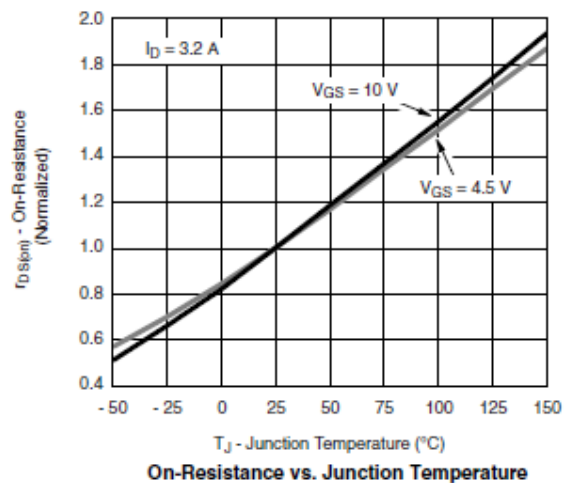
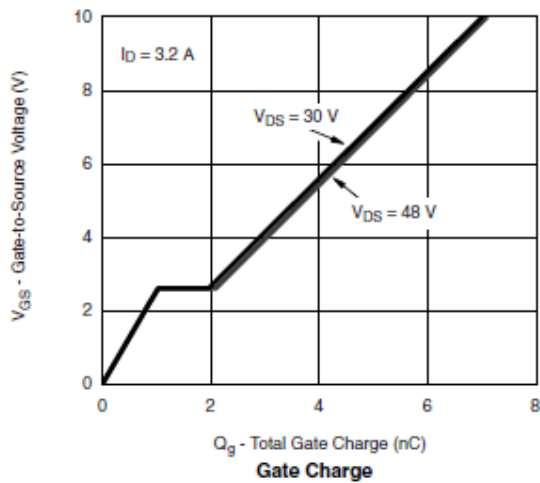
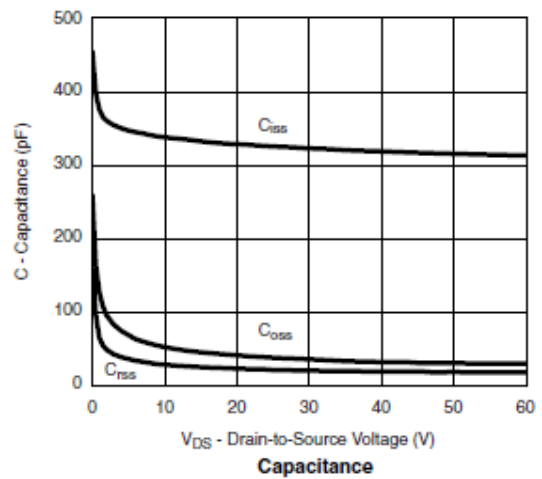
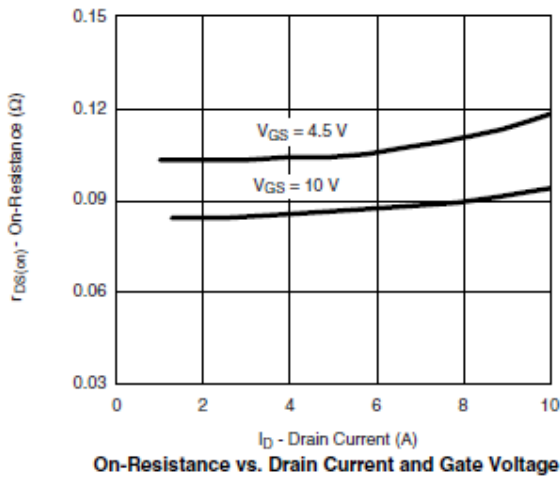
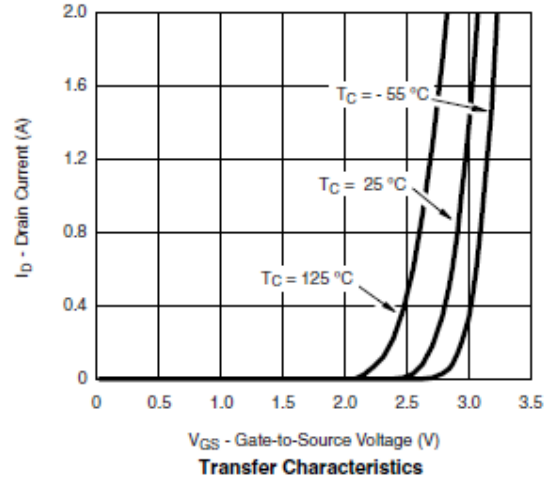
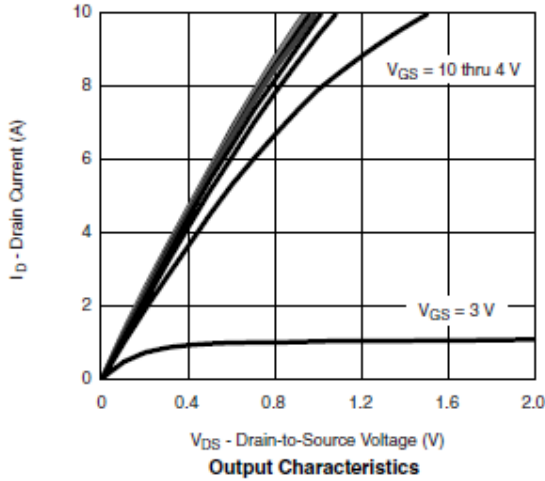
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.7		2.5	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V			1	uA
		V _{DS} =48V, V _{GS} =0V T _J =85°C			5	
On-State Drain Current	I _{D(on)}	V _{DS} ≥ 5V, V _{GS} =4.5V	12			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =6.8A		75	100	mΩ
		V _{GS} =4.5V, I _D =5.6A		90	130	
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =5.3A		12		S
Diode Forward Voltage	V _{SD}	I _S =2.0A, V _{GS} =0V		0.8	1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =48V, V _{GS} =4.5V I _D ≅5A		6	12	nC
Gate-Source Charge	Q _{gs}			2.0		
Gate-Drain Charge	Q _{gd}			3.0		
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V f=1MHz		480		pF
Output Capacitance	C _{oss}			50		
Reverse Transfer Capacitance	C _{rss}			35		
Turn-On Time	t _{d(on)}	V _{DD} =30V, R _L =6.0Ω I _D ≅5.0A, V _{GEN} =10V R _G =3.3V		6	12	ns
	t _r			6	12	
Turn-Off Time	t _{d(off)}			12	20	
	t _f			4	10	

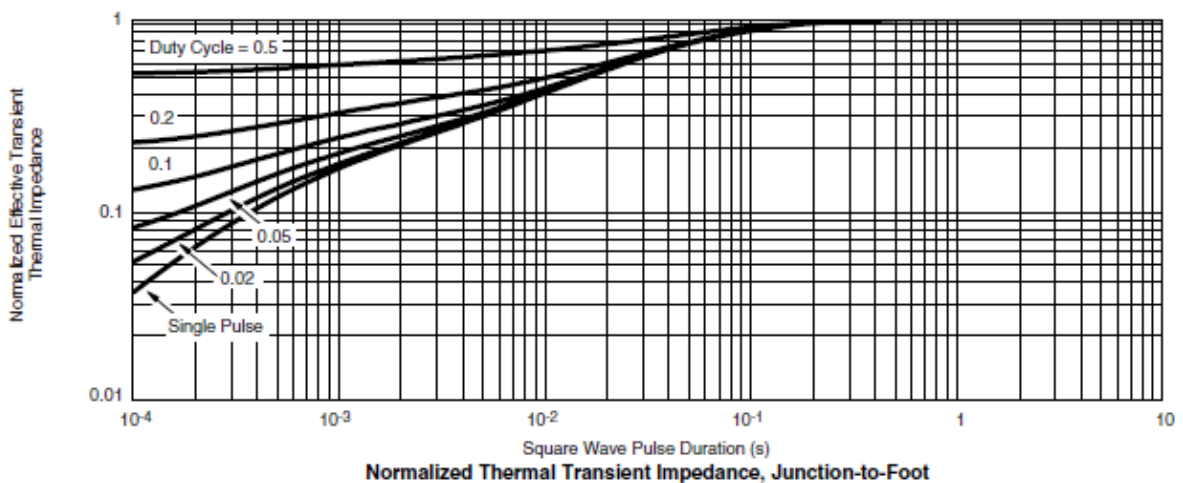
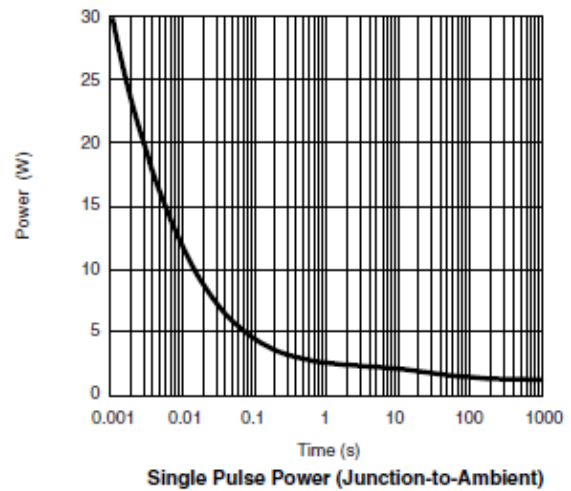
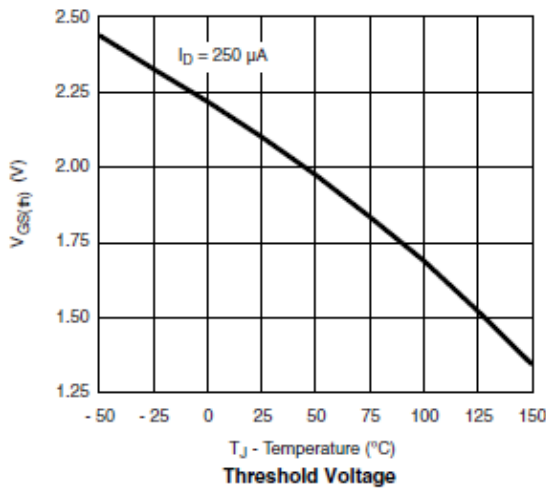
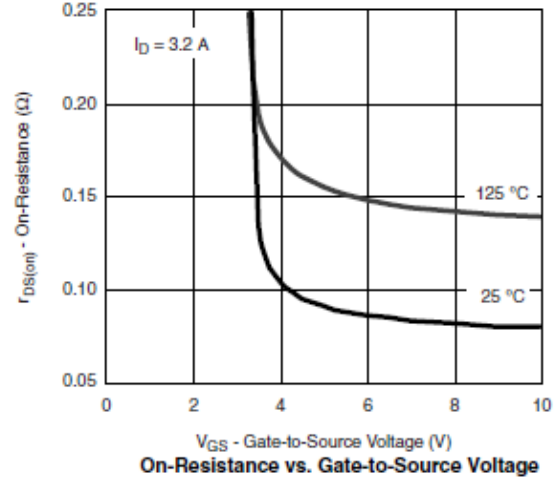
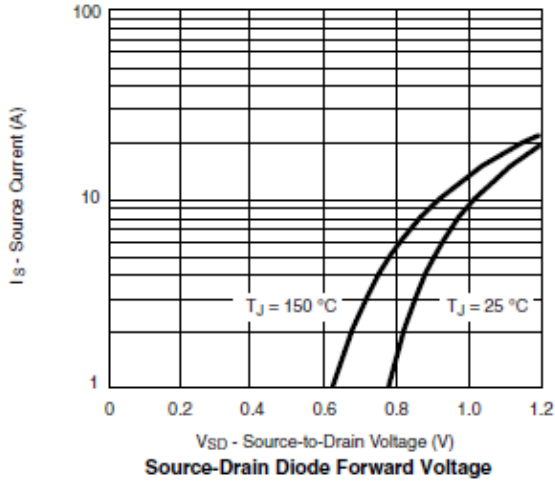


Typical Characteristics





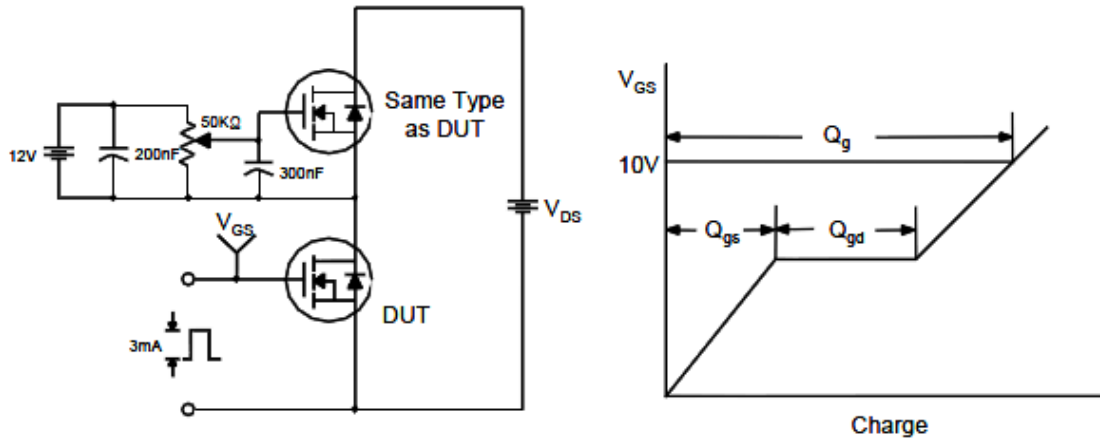
Typical Characteristics



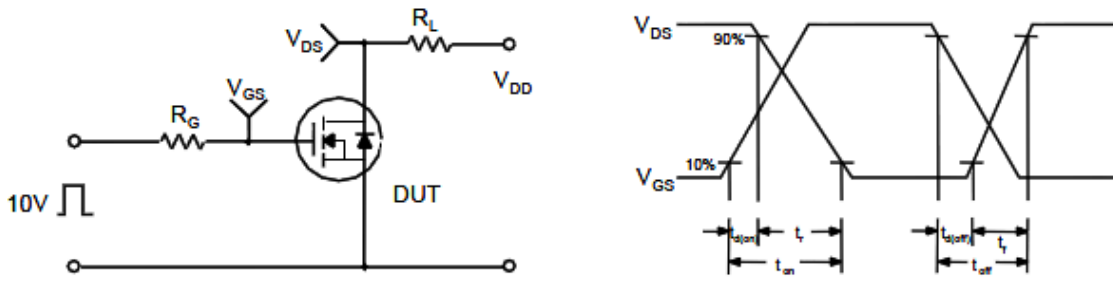


Typical Characteristics

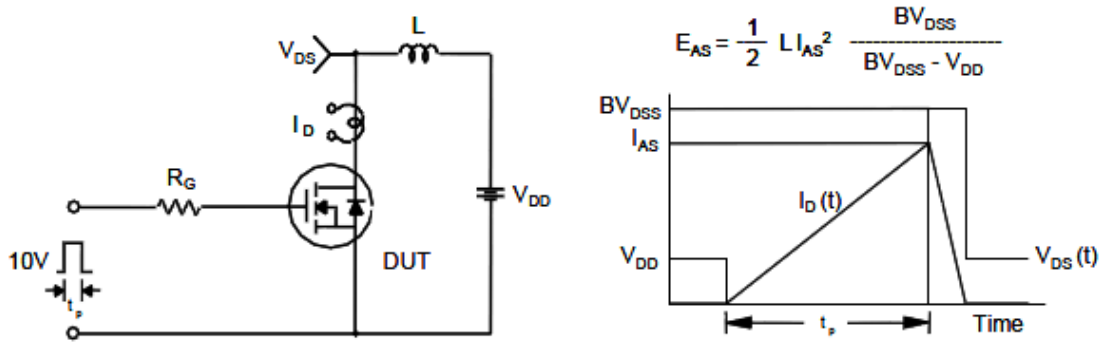
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

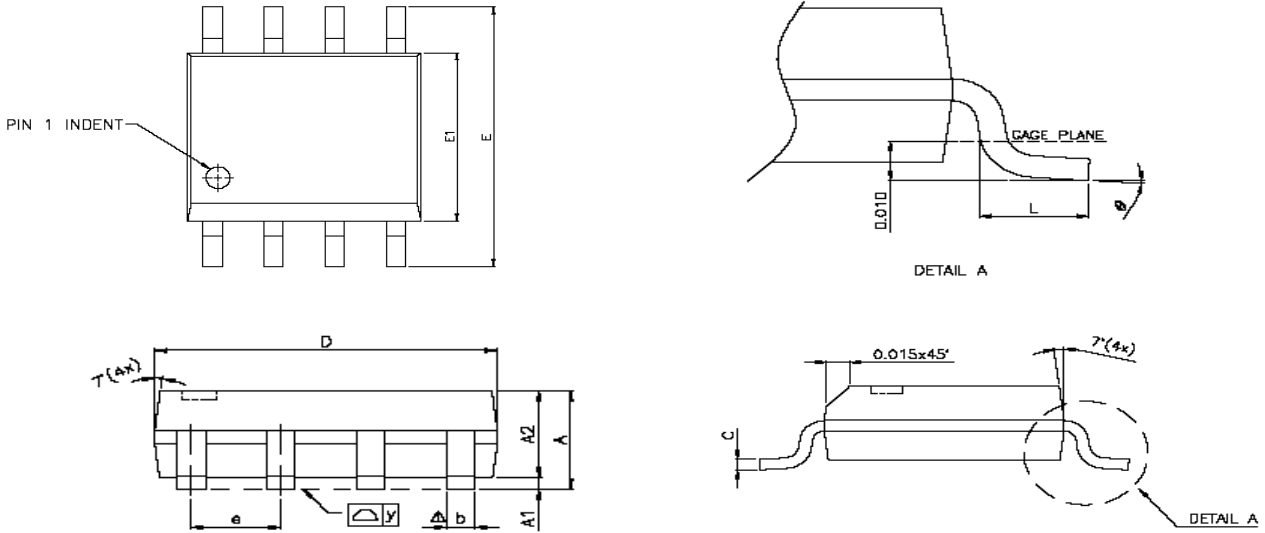


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (SOP-8P)



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
Δy	—	—	0.076	—	—	0.003
θ	0°	—	8°	0°	—	8°

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